

Amendments to the Abstract:

Please replace the Abstract at page 19 with the following amended abstract:

--ABSTRACT OF THE DISCLOSURE

An integrated semiconductor memory is disclosed having ~~[[with]]~~ selection transistors which ~~[[is]]~~ can be formed at a respective ridge. The ridge can be arranged on an insulation layer. In the ridge the ~~[[The]]~~ first source/drain region ~~is arranged~~ can be formed ~~on the insulation layer~~ at ~~[[one]]~~ another lateral end of the ridge ~~and the second source/drain region is arranged on the insulation layer at another lateral end of the ridge~~. The longitudinal sides of the ridge and a top side of the ridge ~~[[is]]~~ can be covered with a layer ~~sequence~~ stack including a gate dielectric and a gate electrode. High write-read currents can be achieved in the on state of the selection transistors and leakage currents occurring in the off state can be reduce. --